

**Amendments to the Specification:**

Please add, beginning at page 11, after line 26, before the last paragraph, the following new paragraph:

Thus, in one embodiment, the present invention provides a first cup-shaped resistive element having a substantially vertical wall, said vertical wall having a top surface of sublithographic thickness; a second cup-shaped resistive element having a substantially vertical wall, said vertical wall having a top surface of sublithographic thickness; a delimiting structure with an aperture having a first portion over the first resistive element and a second portion over the second resistive element; a first memory portion of phase change material in the first portion of said aperture, the first memory portion being in contact with the first resistive element and defining a first contact area of sublithographic dimension, and a second memory portion of phase change material in the second portion of said aperture, the second memory portion being in contact with the second resistive element and defining a second contact area of sublithographic dimension.